

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	(fin with (fet transistor structure)) and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and void and @ad<"20040415"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:33
L2	16	(fin with (fet transistor structure)) and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and void	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:52
L3	28	(fin with (fet transistor structure)) and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and @ad<"20040415"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:47
L4	3977	438/142,156,164,212,585,595.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:52
L5	2	4 and (fin with (fet transistor structure)) and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and void	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:53
L6	205	((huilong near zhu) (bruce near b near doris)).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:53
L7	1	6 and fin and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and void	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/14 14:54

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(fin and (semiconductor near substrate) and (remov\$3 etch\$3) with (SiGe (silicon near germanium)) and (spacer support) and void).clm.	US-PGPUB	OR	ON	2007/04/14 14:55